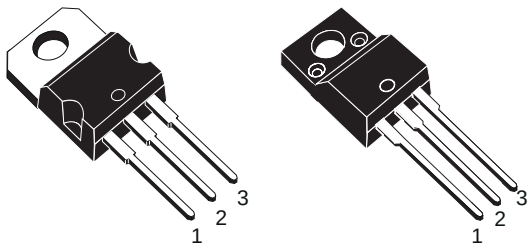
STP3NB100
STP3NB100FP

N-CHANNEL 1000V - 5.3Ω - 3A TO-220/TO-220FP
PowerMesh™ MOSFET

PRELIMINARY DATA

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STP3NB100	1000 V	< 6 Ω	3 A
STP3NB100FP	1000 V	< 6 Ω	3 A

- TYPICAL $R_{DS}(on)$ = 5.3Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED



TO-220 **TO-220FP**

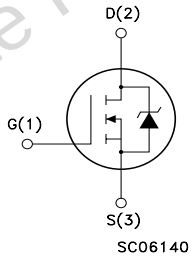
DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprieraty edge termination structure, gives the lowest $R_{DS(on)}$ per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP3NB100	STP3NB100FP	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	1000		V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	1000		V
V_{GS}	Gate- source Voltage	±30		V
I_D	Drain Current (continuos) at T_C = 25°C	3	3 (*)	A
I_D	Drain Current (continuos) at T_C = 100°C	1.9	1.9 (*)	A
I_{DM} (•)	Drain Current (pulsed)	12	12	A
P_{TOT}	Total Dissipation at T_C = 25°C	100	35	W
	Derating Factor	0.8	0.28	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	4.5	4.5	V/ns
V_{ISO}	Insulation Withstand Voltage (DC)	-	2500	V
T_{stg}	Storage Temperature	–65 to 150		°C
T_j	Max. Operating Junction Temperature	150		°C

(•)Pulse width limited by safe operating area

(*)Limited only by maximum temperature allowed

(1)I_{SD} ≤3A, di/dt ≤200A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX.}$

THERMAL DATA

		TO-220	TO-220FP	
Rthj-case	Thermal Resistance Junction-case Max	1.25	3.57	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5		°C/W
T_l	Maximum Lead Temperature For Soldering Purpose	300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	3	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V)	244	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	1000			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating			1	µA
		V_{DS} = Max Rating, T_C = 125 °C			50	µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ±30V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V, I_D = 1.5 A		5.3	6	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, I_D = 1.7 A		2.8		S
C_{iss}	Input Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		700		pF
C_{oss}	Output Capacitance			80		pF
C_{rss}	Reverse Transfer Capacitance			8		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = 500 V, I_D = 1.5 A		18		ns
t_r	Rise Time	R_G = 4.7Ω V_{GS} = 10 V (see test circuit, Figure 3)		12		ns
Q_g	Total Gate Charge	V_{DD} = 800V, I_D = 3 A,		22	30	nC
Q_{gs}	Gate-Source Charge	V_{GS} = 10V		6		nC
Q_{gd}	Gate-Drain Charge			10.5		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	V_{DD} = 800V, I_D = 3 A,		22		ns
t_f	Fall Time	R_G = 4.7Ω, V_{GS} = 10V (see test circuit, Figure 5)		28		ns
t_c	Cross-over Time			30		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				3	A
I_{SDM} (1)	Source-drain Current (pulsed)				12	A
V_{SD} (2)	Forward On Voltage	I_{SD} = 3 A, V_{GS} = 0			1.6	V
t_{rr}	Reverse Recovery Time	I_{SD} = 3 A, di/dt = 100A/µs,		580		ns
Q_{rr}	Reverse Recovery Charge	V_{DD} = 100V, T_j = 150°C (see test circuit, Figure 5)		2.9		µC
I_{RRM}	Reverse Recovery Current			10		A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

Fig. 1: Unclamped Inductive Load Test Circuit

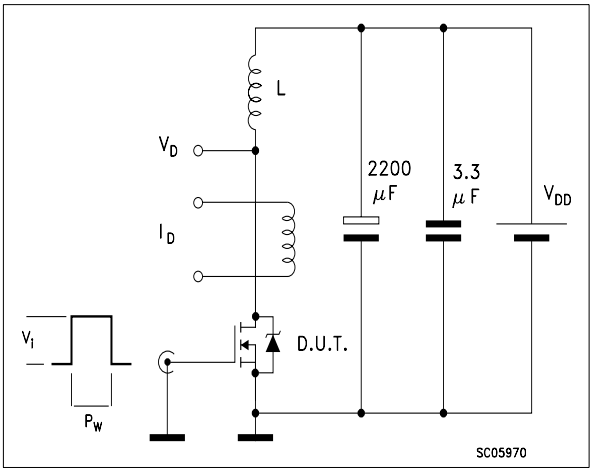


Fig. 2: Unclamped Inductive Waveform

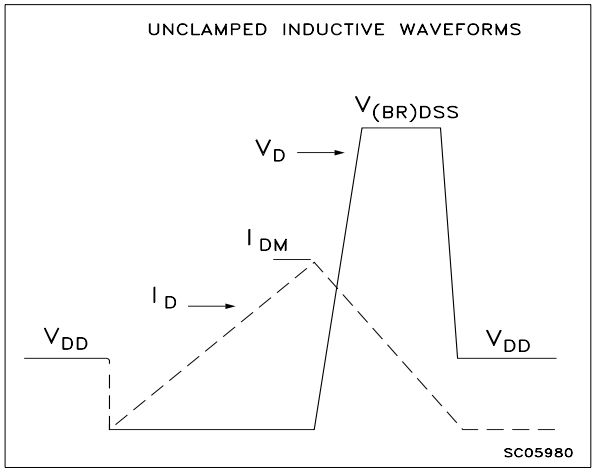


Fig. 3: Switching Times Test Circuit For Resistive Load

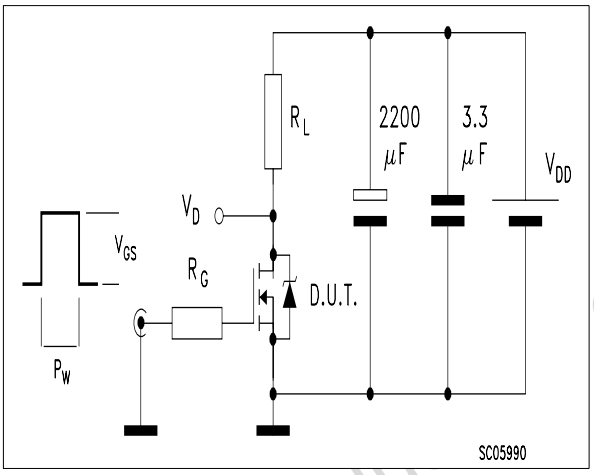


Fig. 4: Gate Charge test Circuit

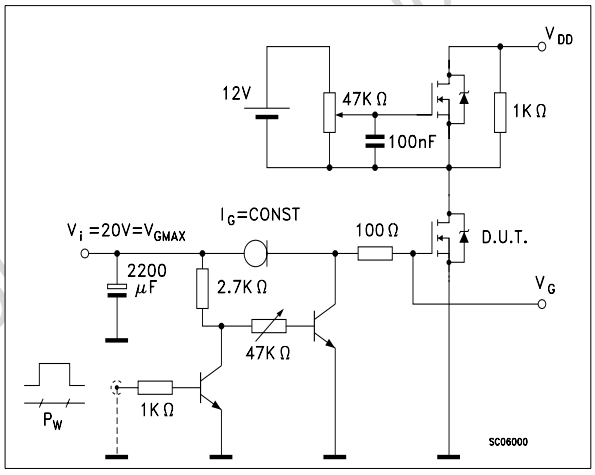
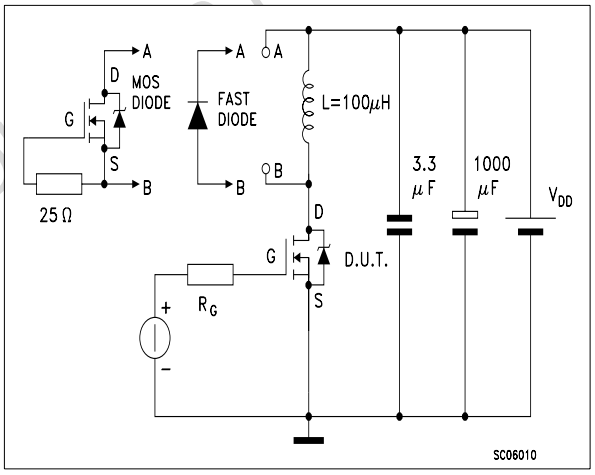
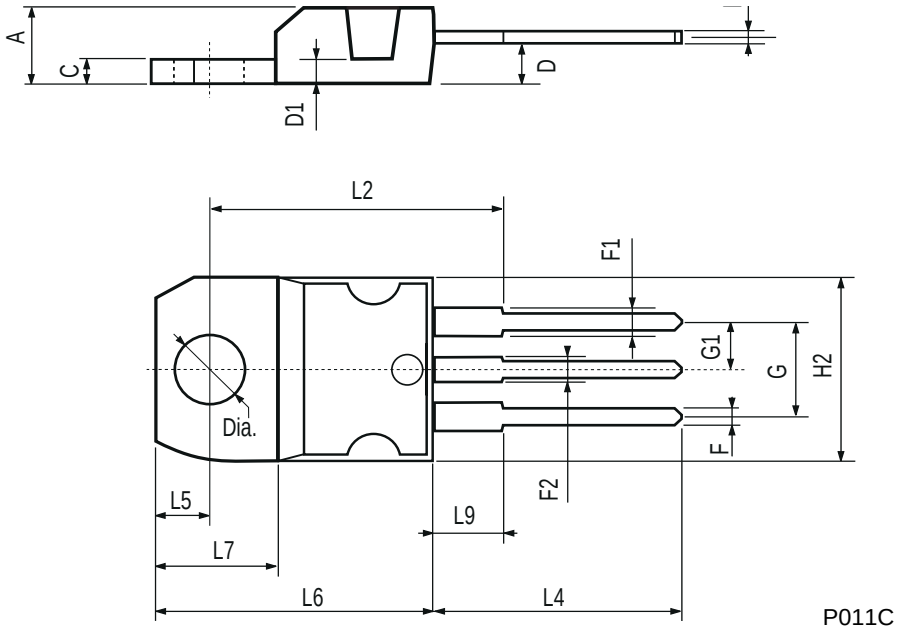


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126